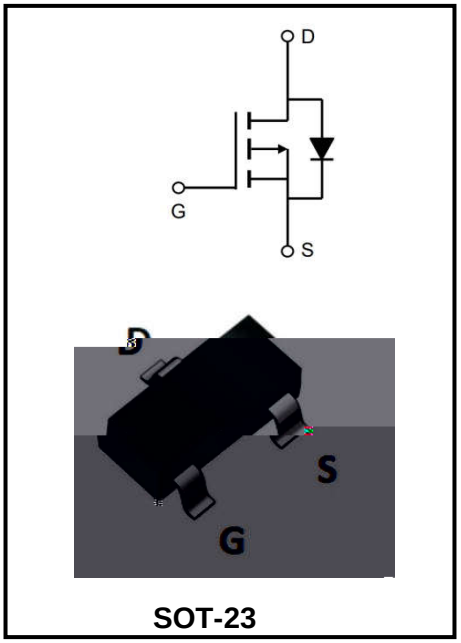
	-4.1A
	-20V



SOT-23

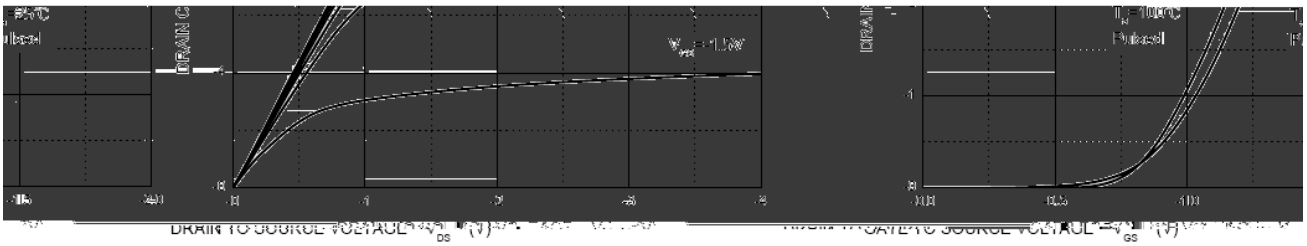
♦TrenchFET Power MOSFET
♦Load Switch for Portable Devices
♦DC/DC Converter.

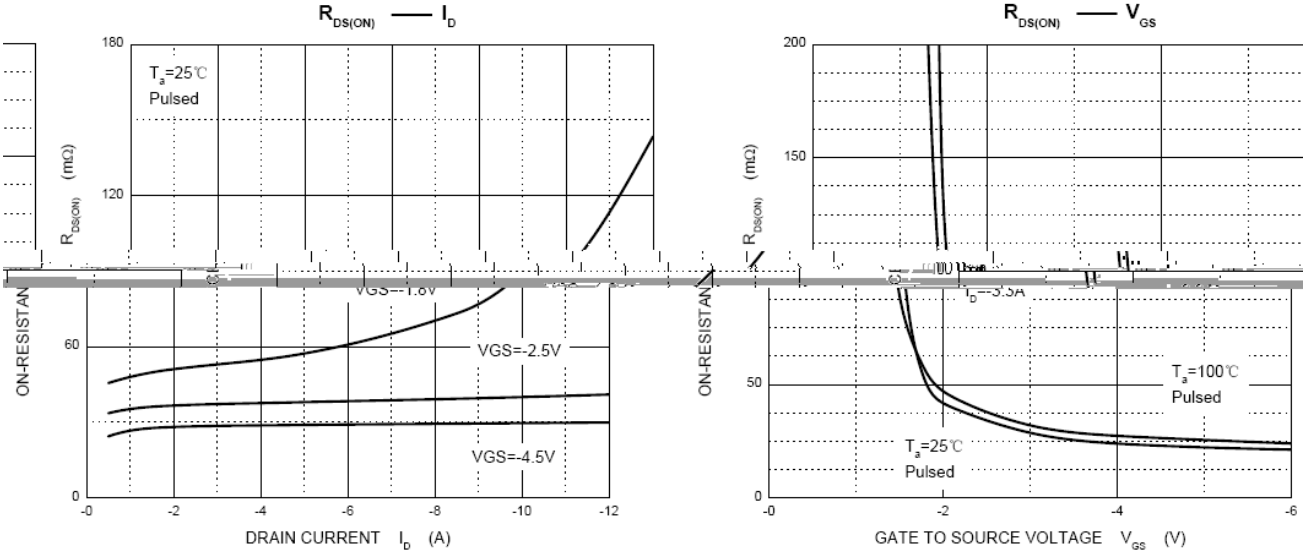
♦SOT-23 Small Outline Plastic Package.
♦Epoxy UL: 94V-0.
♦Mounting Position: Any.

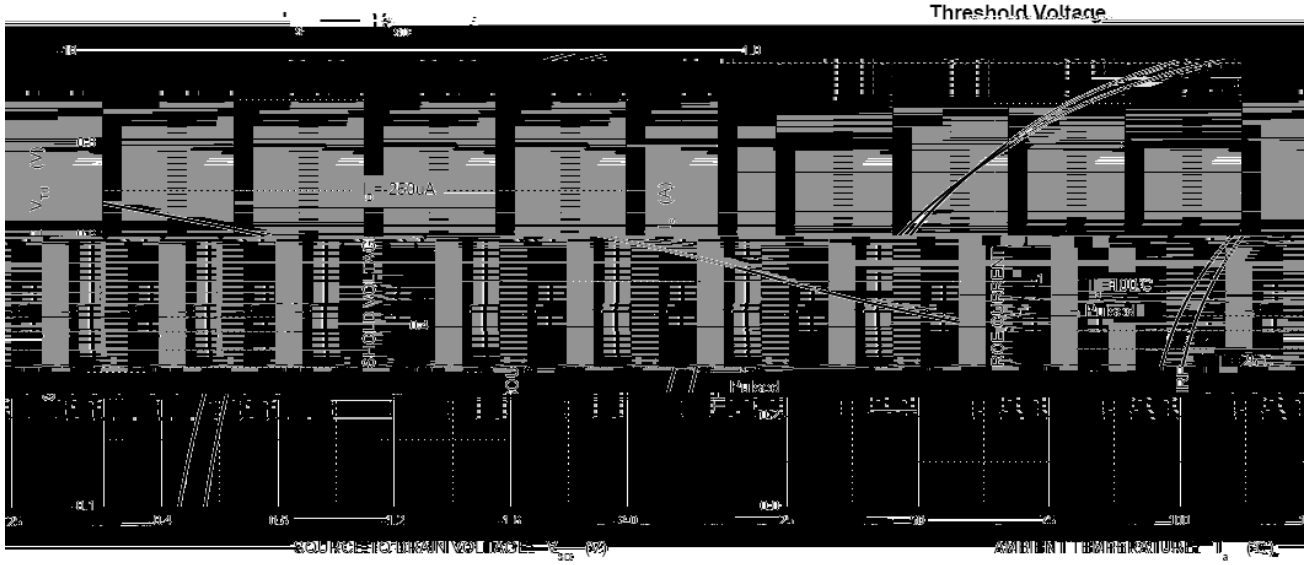
Drain-Source Voltage		-20	
Gate-Source Voltage		Ñ12	
Continuous Drain Current		-4.1	
Continuous Source-Drain Diode Current		-0.8	
Power Dissipation		350	
Junction Temperature		150	
Storage Temperature		-50-+150	
Thermal Resistance From Junction to Ambient		357	

Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=-250uA	-20	-	-
Gate-Threshold voltage	V_{DS}=V_{GS}, I_D=-250uA	-0.5	-	-0.9
Gate-body Leakage	V_{DS}=0V, V_{GS}=Ñ12V	-	-	Ñ100
Zero Gate Voltage Drain current	V_{DS}=-8V, V_{GS}=0V	-	-	-1
Drain-Source On-Resistance(a)	V_{GS}=-4.5V, I_D=-3.5A	-	30	45
	V_{GS}=-2.5V, I_D=-3.0A	-	40	60
	V_{GS}=-1.8V, I_D=-2A	-	60	90
Forward trans conductance(a)	V_{DS}=-5V, I_D=-4A	6	-	-
Input capacitance	V_{DS}=-4V V_{GS}=0V f=1MHz	-	740	-
Output capacitance		-	290	-
Reverse Transfer capacitance		-	190	-

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$R_{DS(ON)}$ —— I_D
T_a=25℃
Pulsed
VGS=-2.5V
VGS=-4.5V
ON-RESISTANCE $R_{DS(ON)}$ (mΩ)
DRAIN CURRENT I_D (A)
$R_{DS(ON)}$ —— V_{GS}
T_a=100℃
Pulsed
T_a=25℃
Pulsed
GATE TO SOURCE VOLTAGE V_{GS} (V)

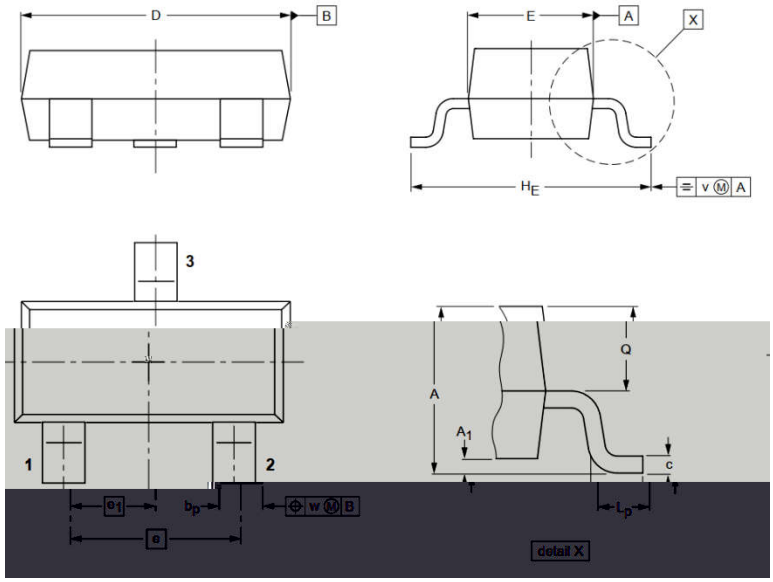

Threshold Voltage
I_D=-250uA

Ordering information

Package	Packing Description	Base Quantity	Packing Quantity
SOT-23	Tape/Reel,7”reel	3000pcs/Reel	24000PCS/Box 120000PCS/Carton

Package Dimensions

SOT-23



Dim.	Millimeter (mm)		mil	
	Min.	Max.	Min.	Max.
A	0.9	1.15	35	45
A1	0.1		3.9	
bp	0.38	0.48	15	19
C	0.09	0.15	3.54	5.9
D	2.8	3.0	110	118
E	1.2	1.4	47	55
E	1.9		75	

The recommended mounting pad size

